Silicon NPN Power Transistors 2SC2690 2SC2690A

DESCRIPTION

・With TO-126 package
・Complement to type 2SA1220/1220A

APPLICATIONS

・For use in audio and radio frequency power amplifiers

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

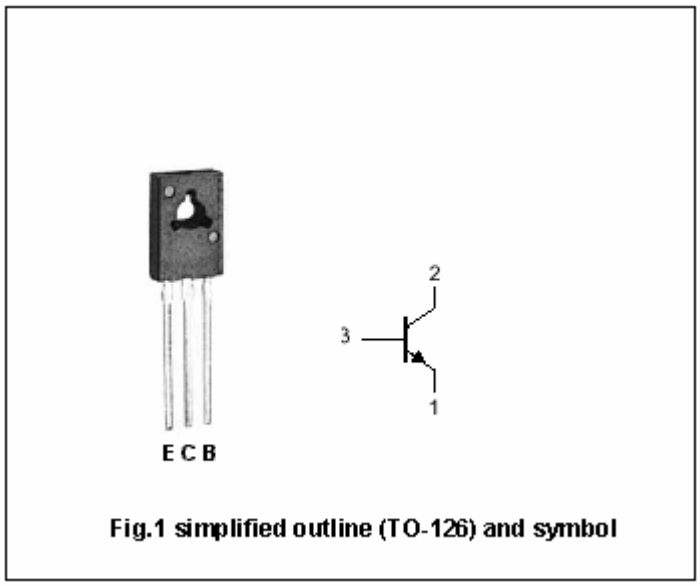

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC2690	Open emitter	120	V
		2SC2690A		160	
V_{CEO}	Collector-emitter voltage	2SC2690	Open base	120	V
		2SC2690A		160	V
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			1.2	A
I_{CM}	Collector current-Peak			2.5	A
I_B	Base current			0.3	A
P_D	Total power dissipation		T_a=25℃	1.2	W
			T_C=25℃	20	
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55～+150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=1A; I_B=0.2A			0.7	V
V_{BEsat}	Base-emitter saturation voltage	I_C=1A ;I_B=0.2A			1.3	V
I_{CBO}	Collector cut-off current	V_{CB}=120V; I_E=0			1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=3V; I_C=0			1	μA
h_{FE-1}	DC current gain	I_C=5mA ; V_{CE}=5V	35			
h_{FE-2}	DC current gain	I_C=0.3A ; V_{CE}=5V	60		320	
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=10V f=1MHz		19		pF
f_T	Transition frequency	I_C=0.2A ; V_{CE}=5V		155		MHz

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	100-200	160-320

PACKAGE OUTLINE

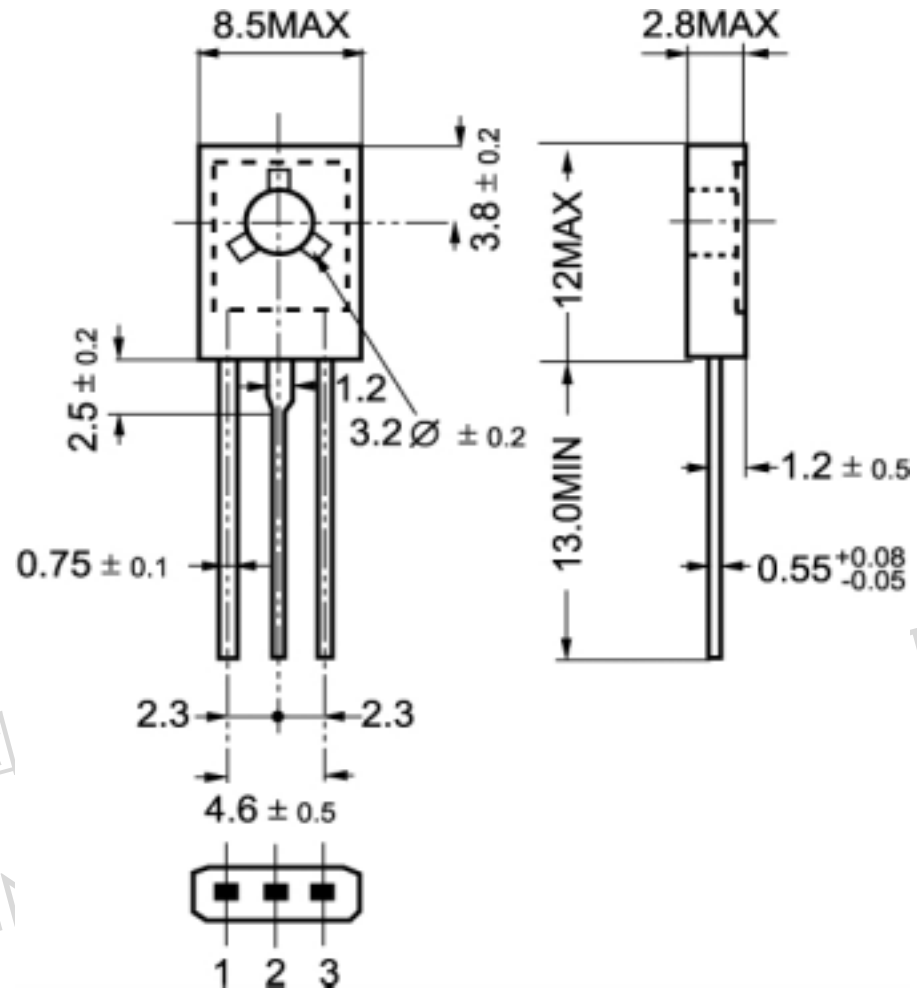

Fig.2 Outline dimensions

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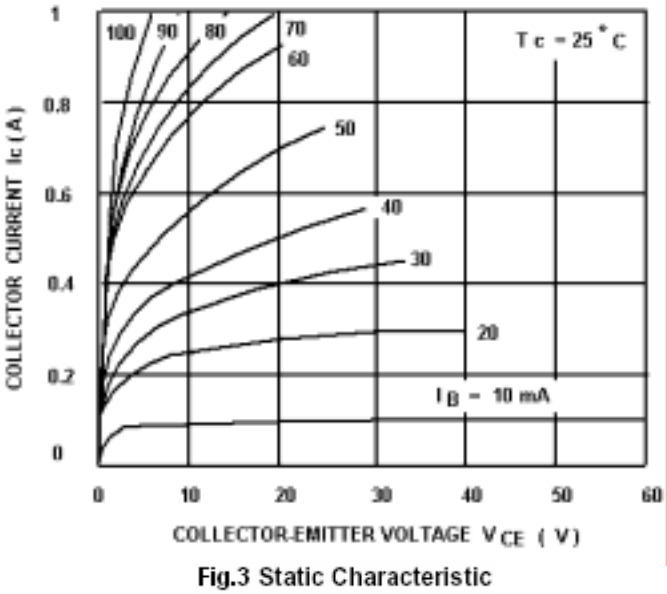

Fig.3 Static Characteristic

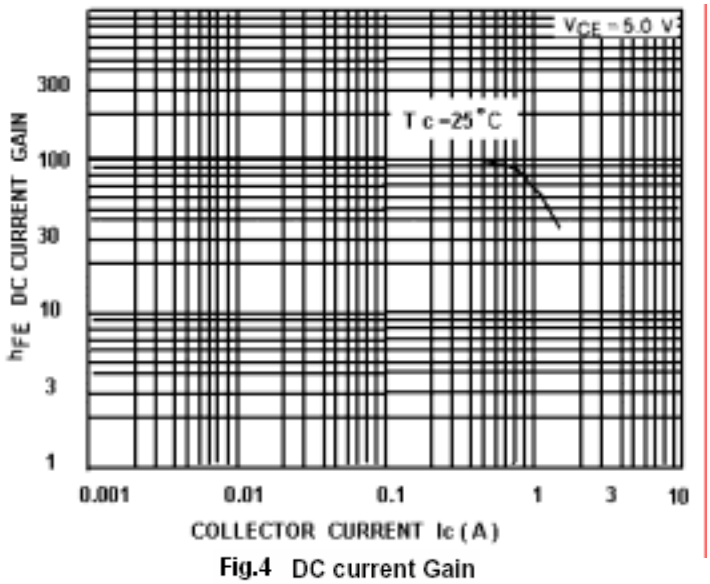

Fig.4 DC current Gain

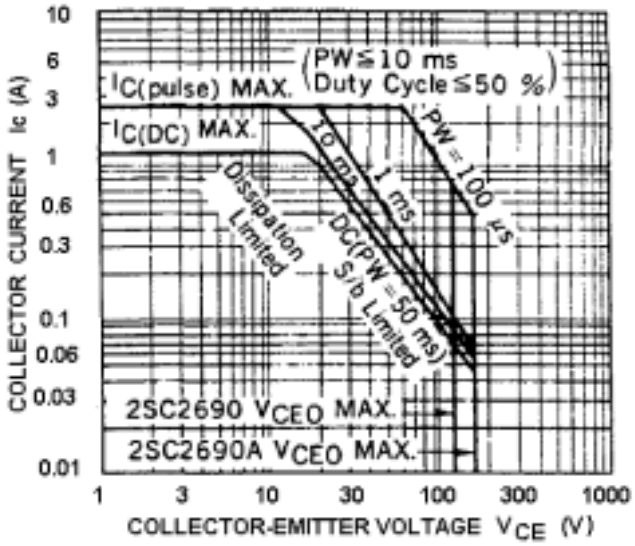

Fig.5 Safe Operating Area